



Gretsi

**15ème école d'été de Peyresq**  
*en traitement du signal et des images*

**Peyresq, du 21 au 27 juin 2020**

## Physique d'acquisition d'images

Capteurs d'images - Jérôme Vaillant

Imagerie non-conventionnelle et co-conception – Corinne Fournier

### Agenda



- (Brief) Introduction to image sensors
  - The ubiquitous CMOS image sensor
  - Smartphone camera: a co-design system
- What is a pixel?
  - How does it work
  - Design and fabrication
  - Optical elements
  - Implementation in a matrix
  - Noises
- Un-conventional / non-visible pixels
  - Depth sensing with pixels
  - Infrared pixels

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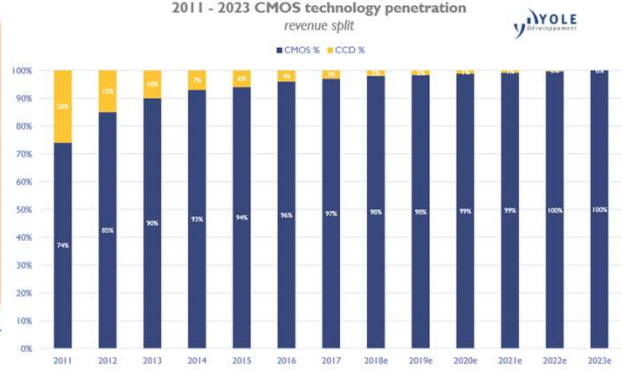
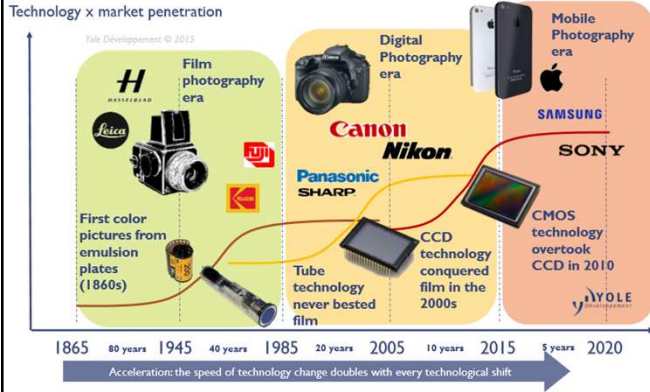
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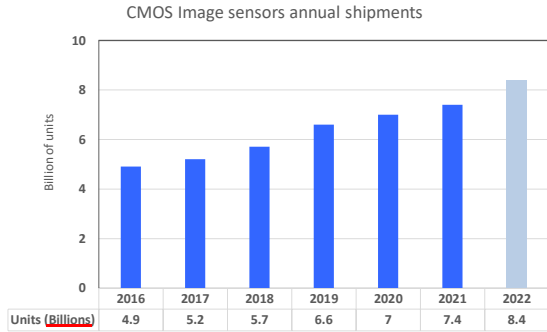
# What's (CMOS) image sensor?



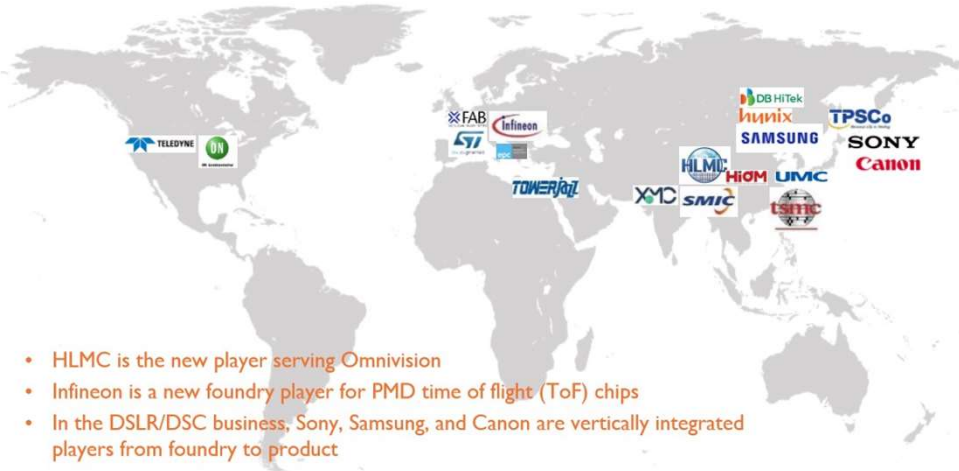
- Array of transducers (pixels) converting photons to electrons
  - CCD: merely a matrix of pixels only => electronics is outside the chip
  - CMOS: integrated circuit
- Brief history:



# CMOS image sensors today

# IMAGE SENSOR FOUNDRIES - GEOGRAPHIC MAPPING



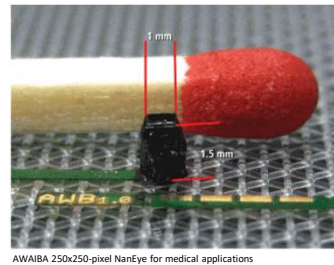
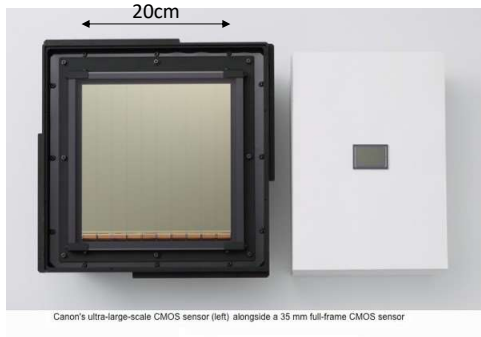
- HLMC is the new player serving Omnivision
- Infineon is a new foundry player for PMD time of flight (ToF) chips
- In the DSLR/DSC business, Sony, Samsung, and Canon are vertically integrated players from foundry to product

**YOLO**  
Développement  
| Status of the CIS industry | www.yole.fr | ©2018

## Overview of pixels zoology



- Pixel size from 200µm down to 0.61µm !
- Image definition from 0.3Mpix to 120Mpix
- Image sensor surface from <math>2 \times 1.5 \text{ mm}^2</math> up to 200x200mm<sup>2</sup>



## Agenda

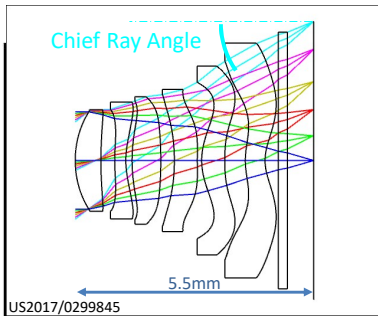


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## A camera in less than 1 cm<sup>3</sup>



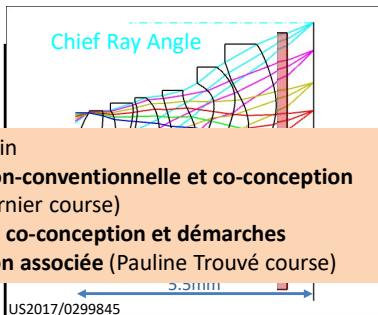
# Optimized objective



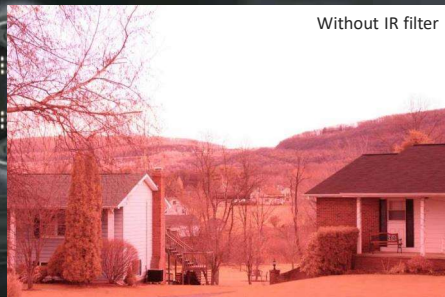
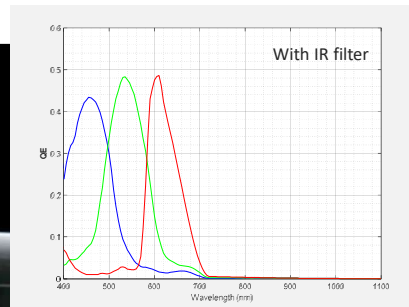
Six-element lens  
f/1.8 aperture



# Optimized objective with IR cut filter

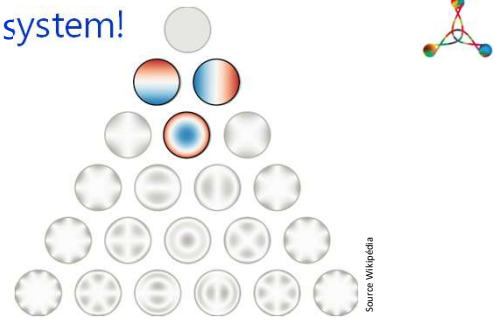


More details in  
 - **Imagerie non-conventionnelle et co-conception**  
 (Corinne Fournier course)  
 - **Modèles en co-conception et démarches d'optimisation associée**  
 (Pauline Trouvé course)



## Smartphone camera: a basic adaptive optics system!

- Modern cameras are 3-modes AO systems
  - Optical Image Stabilization (OIS) is a tip-tilt corrector
  - Autofocus is a defocus corrector



- Extended Depth of Focus (eDoF) uses wavefront coding and image deconvolution
  - Introduction of phase plate in objective
  - PSF with low dependence in  $z$ , but enlarged in  $x,y$  (image plane)
  - *New paradigm for imaging systems*, Cathey et al., <https://doi.org/10.1364/AO.41.006080>

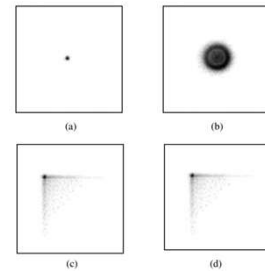
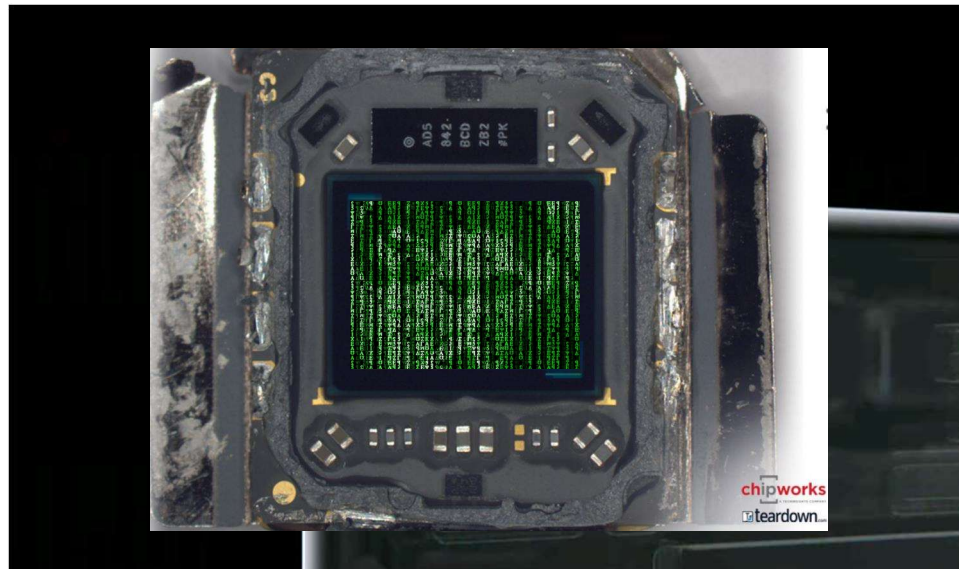
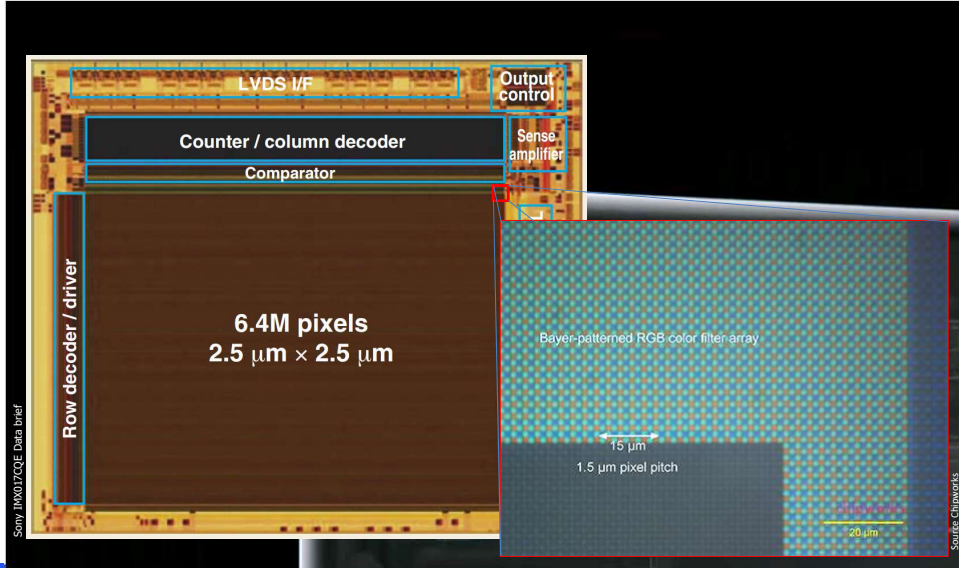


Figure 3. The PSF of the traditional imaging systems (a) in focus and (b) out of focus, and the system with an extended depth of field (c) and (d) for the same focus settings.

## Focus on image acquisition: the pixel matrix



# CMOS image sensor: a pixel array with circuits on a single chip *System on Chip (SoC)*



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## What is a pixel ?



It depends...

on who you are taking to

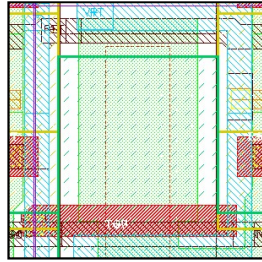
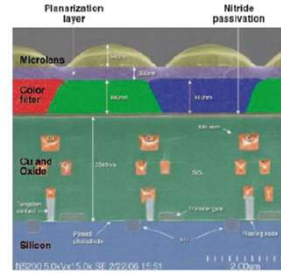
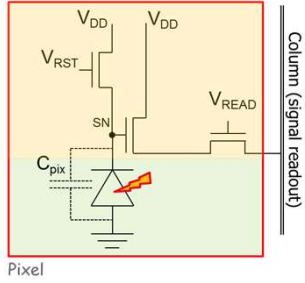
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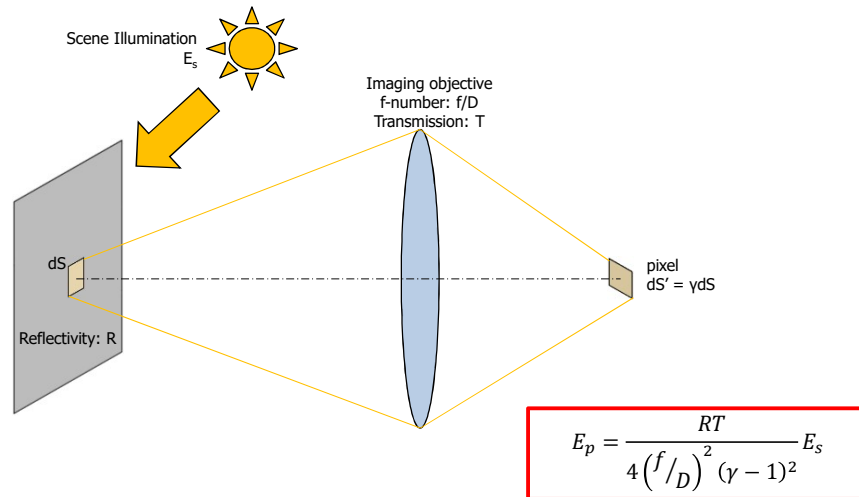
# Various representations of a pixel



Before let's quantify the amount on light hitting a pixel



## How to calculate the illumination of a pixel?



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## Number of photons per pixel

- Main objective with  $f/D=8$  and a transmission of  $T=90\%$
- Landscape photography, so  $|\gamma| \ll 1$
- Maximum sunlight illumination:  $E_s=100,000$  lux
- Average reflectivity of the scene  $R=18\%$
- Pixel pitch  $2\mu\text{m}$
- Integration time  $1/500$  s



$$E_p = \frac{RT}{4 \left(\frac{f}{D}\right)^2} E_s \approx 65 \text{ lux}$$

$$N_{\text{photons}} = E_p \times p_{\text{pixel}}^2 \times \tau_{\text{int}} \approx 12500 \text{ photons/pixel}$$

$$1 \text{ lux} \approx 10^{16} \text{ photons} \cdot \text{s}^{-1} \cdot \text{m}^{-2} \quad (\text{sunlight at Earth ground integrated over } 400\text{-}650\text{nm})$$

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## Number of photons per pixel



- Main objective with  $f/D=4$  and a transmission of  $T=90\%$
- Landscape photography, so  $|\gamma| \ll 1$
- Maximum sunlight illumination:  $E_s=10,000 \text{ lux}$
- Average reflectivity of the scene  $R=18\%$
- Pixel pitch  $2\mu\text{m}$
- Integration time  $1/100 \text{ s}$



$$E_p = \frac{RT}{4\left(\frac{f}{D}\right)^2} E_s \approx 12 \text{ lux}$$

$$N_{\text{photons}} = E_p \times p_{\text{pixel}}^2 \times \tau_{\text{int}} \approx 2500 \text{ photons/pixel}$$

## Number of photons per pixel



- Main objective with  $f/D=2.8$  and a transmission of  $T=90\%$
- Landscape photography, so  $|\gamma| \ll 1$
- Maximum sunlight illumination:  $E_s=50 \text{ lux}$
- Average reflectivity of the scene  $R=18\%$
- Pixel pitch  $2\mu\text{m}$
- Integration time  $1/30 \text{ s}$



$$E_p = \frac{RT}{4\left(\frac{f}{D}\right)^2} E_s \approx 0.25 \text{ lux}$$

$$N_{\text{photons}} = E_p \times p_{\text{pixel}}^2 \times \tau_{\text{int}} \approx 350 \text{ photons/pixel}$$

## Number of photons per pixel



- Main objective with  $f/D=16$  and a transmission of  $T=90\%$
- Macro photography,  $\gamma = -1$
- Maximum sunlight illumination:  $E_s=10\,000\text{ lux}$
- Average reflectivity of the scene  $R=18\%$
- Pixel pitch  $2\mu\text{m}$
- Integration time  $1/100\text{ s}$



$$E_p = \frac{RT}{4\left(\frac{f}{D}\right)^2 \times (\gamma-1)^2} E_s \approx 0.40\text{ lux}$$

$$N_{\text{photons}} = E_p \times p_{\text{pixel}}^2 \times \tau_{\text{int}} \approx 160\text{ photons/pixel}$$

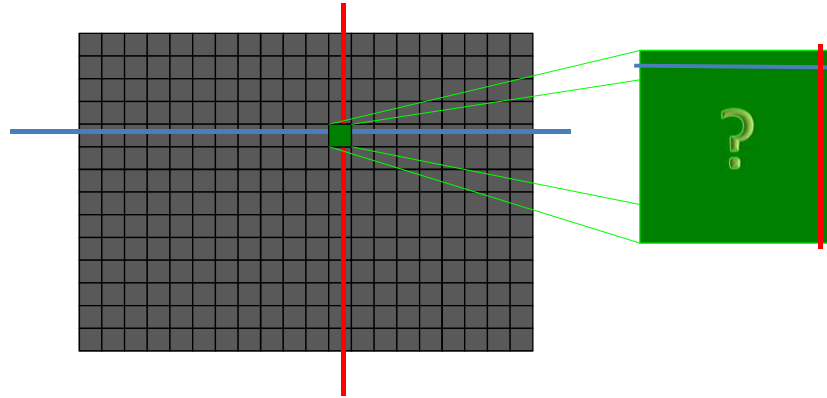
Keep in mind for noise part

## Agenda

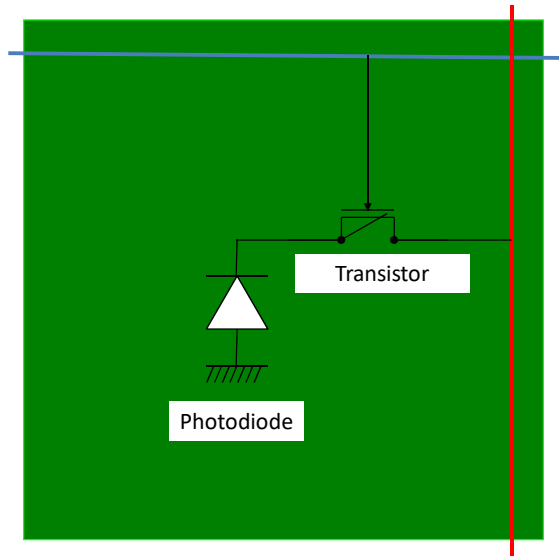


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# What do we need to make a pixel?



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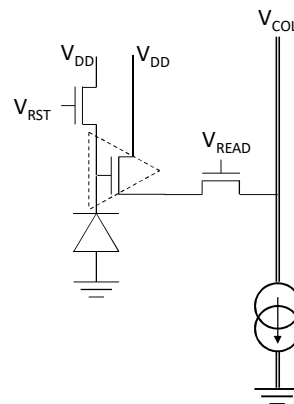


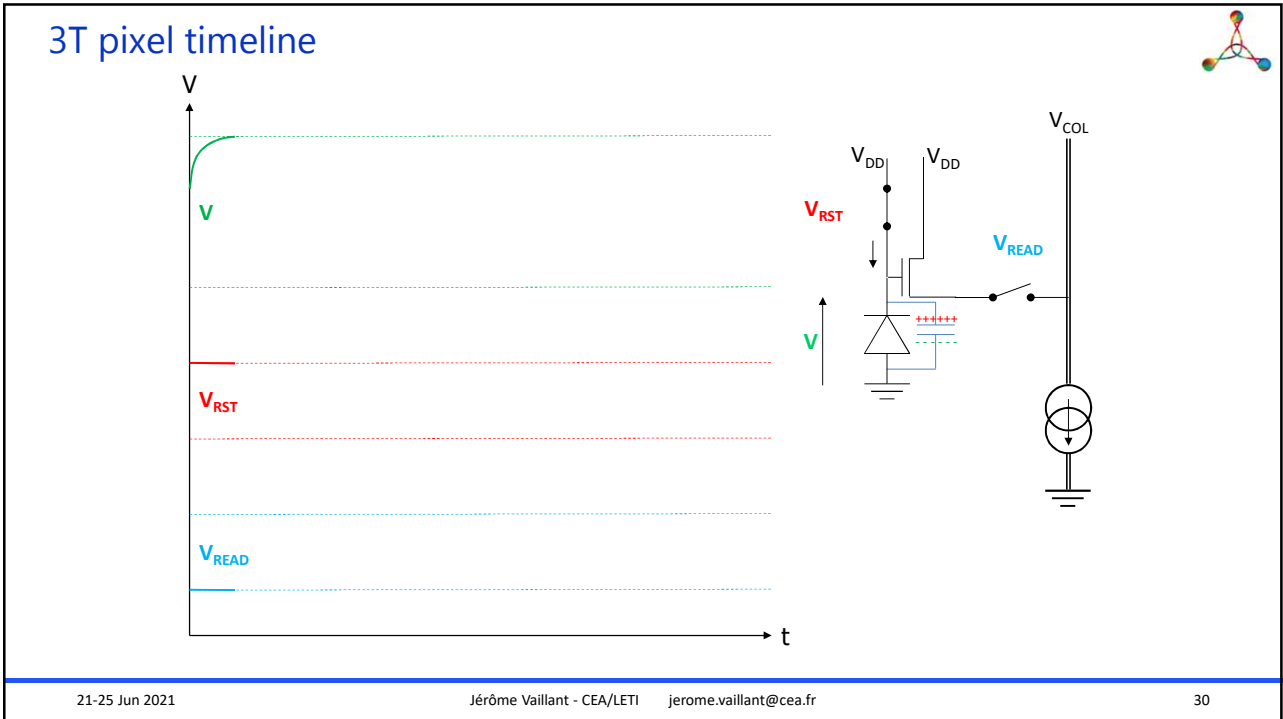
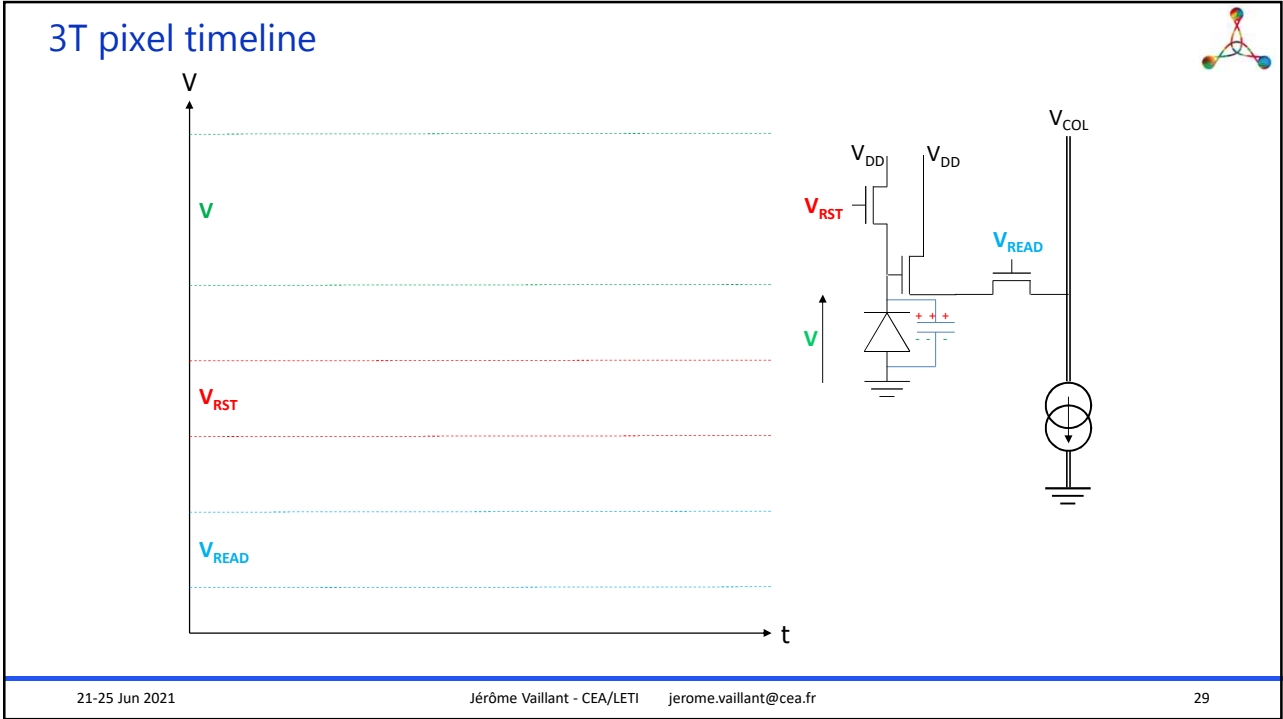
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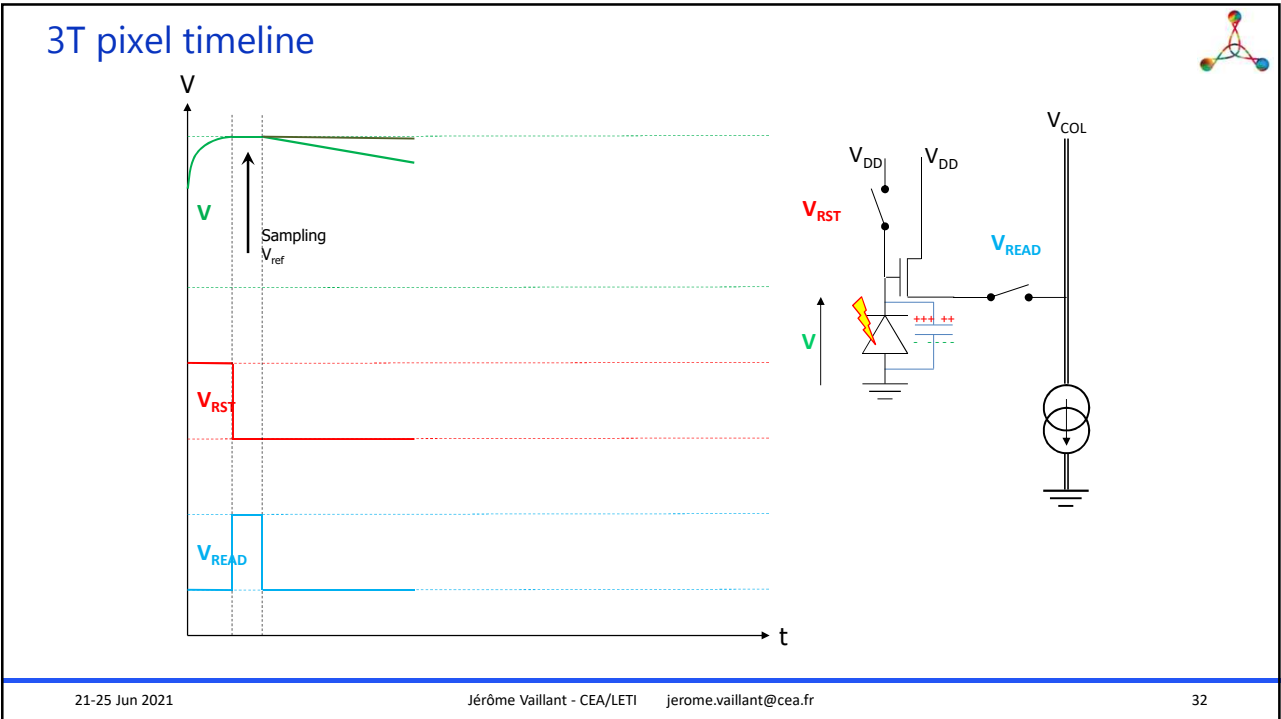
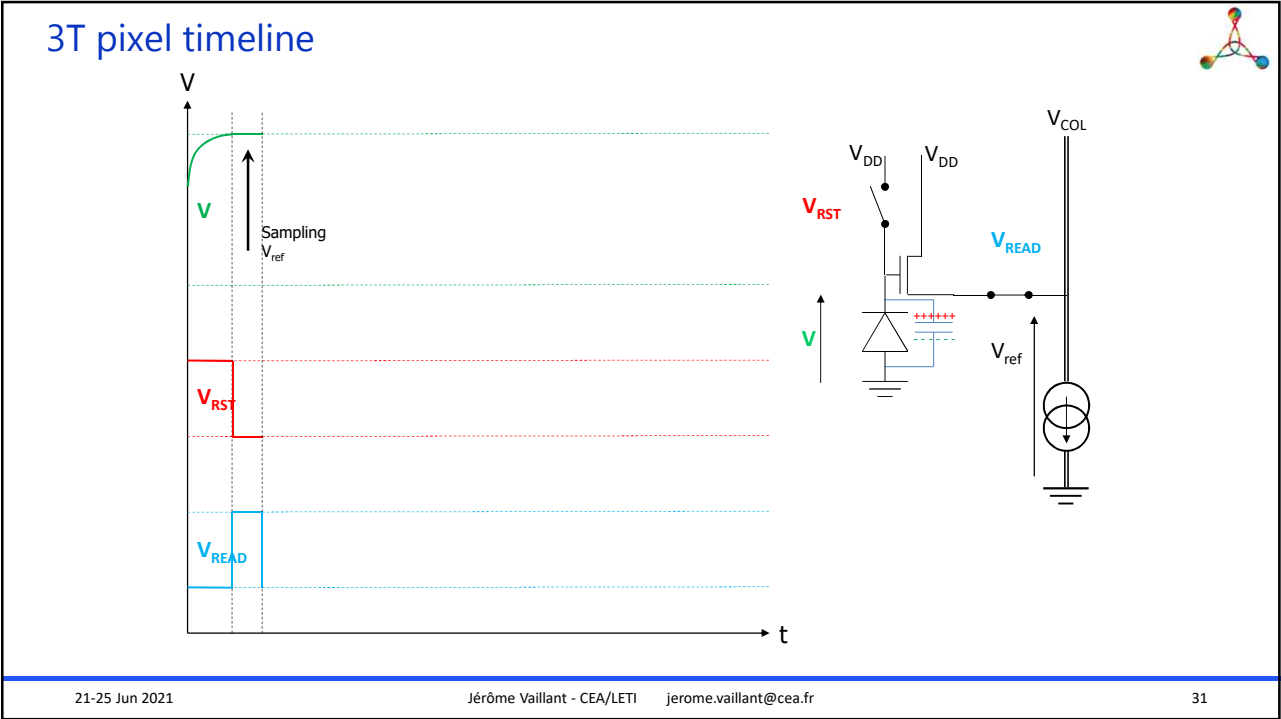
## Active Pixel Sensor (APS)



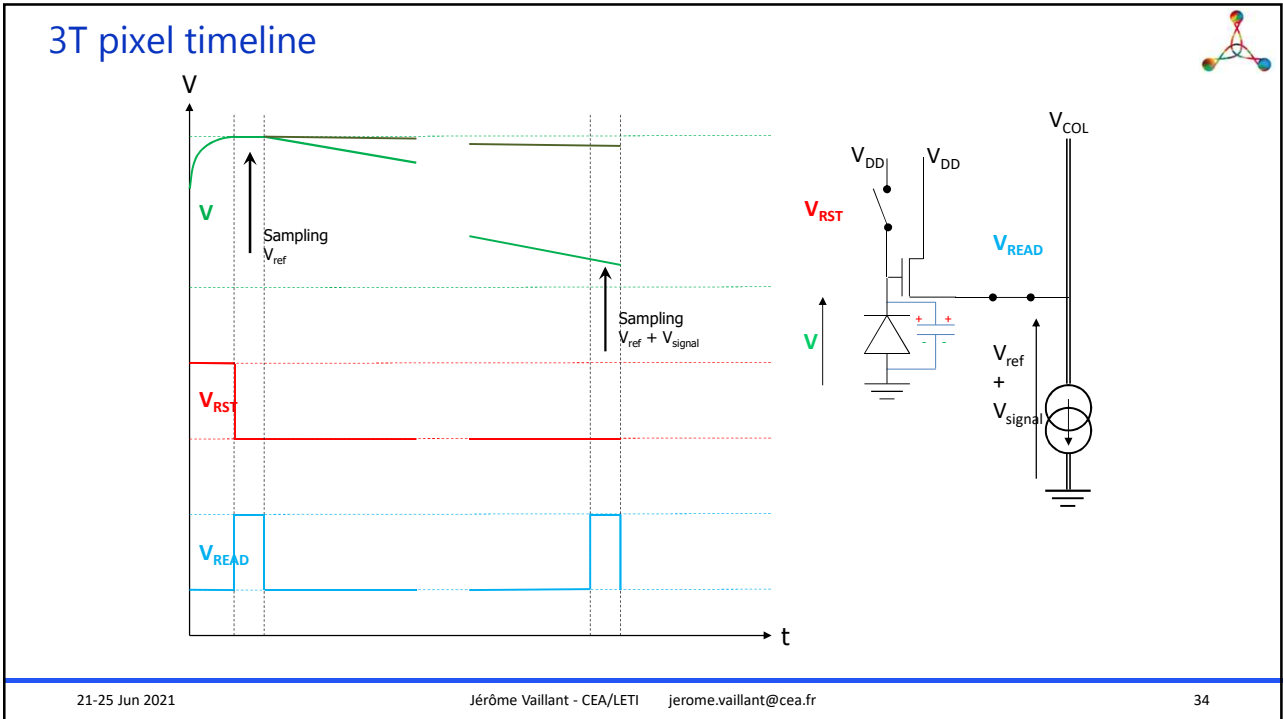
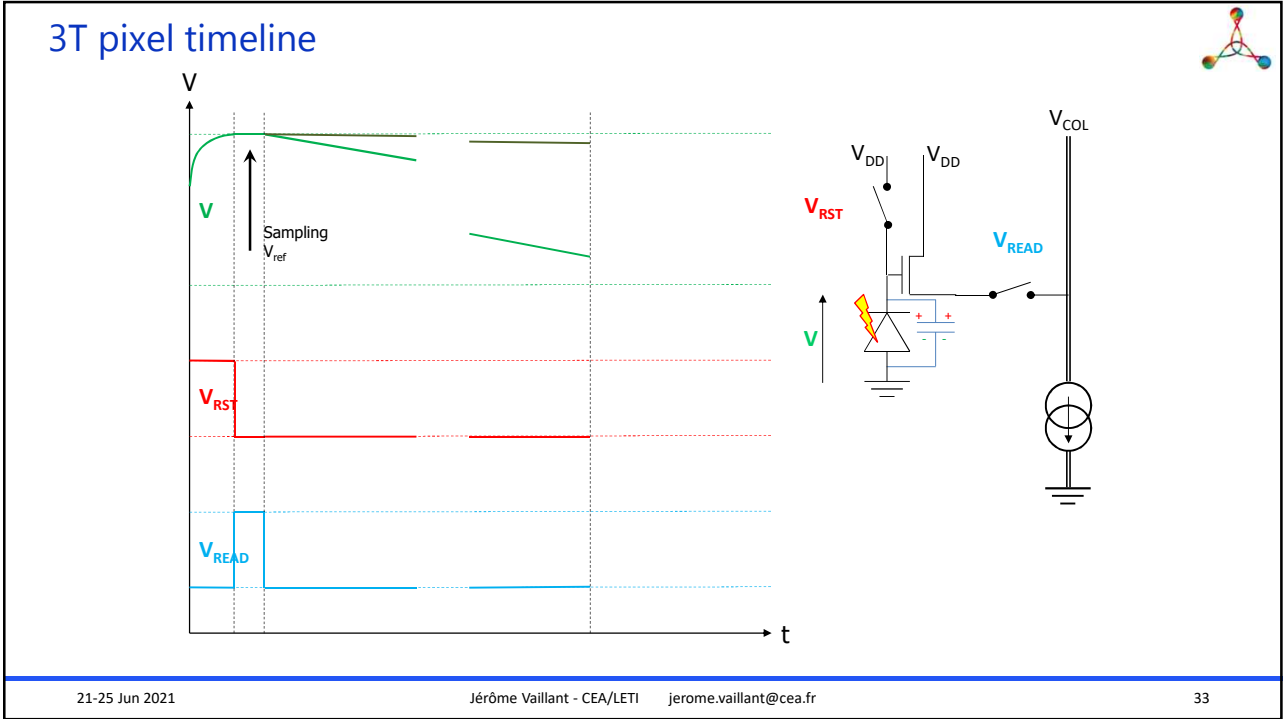
- 3 transistors pixel denoted 3T
  - Photodiode
  - Reset transistor
  - Read (addressing) transistor
  - Source follower transistor

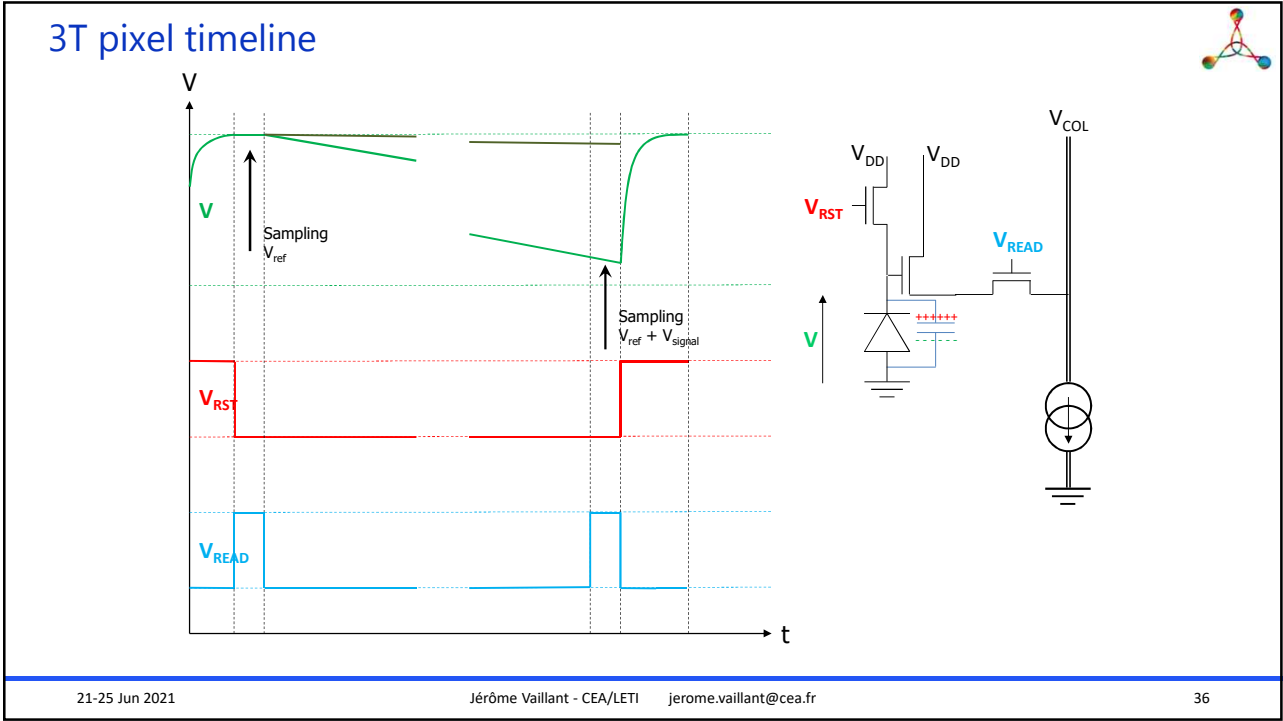
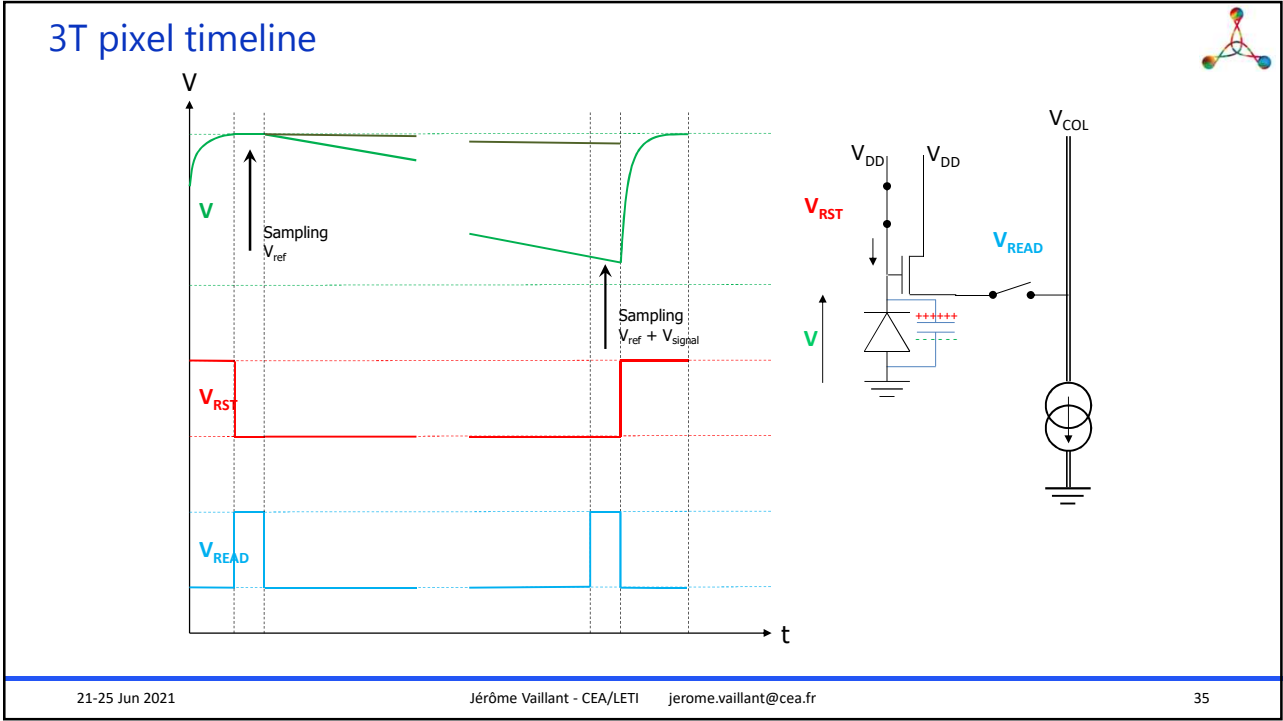












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## How to do it?

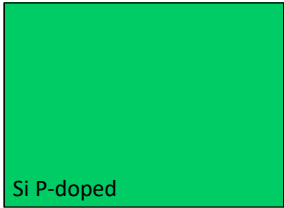


- How to design and process pixel on silicon wafer?
  - How to do a photodiode ?
  - How to do a transistor ?

## Process for a photodiode



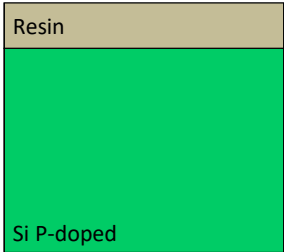
- PN junction
  - Based on P-doped silicon substrate (e.g. dopant Bore)
  - Local ion implant of N-doping (e.g. Phosphor)



## Process for a photodiode



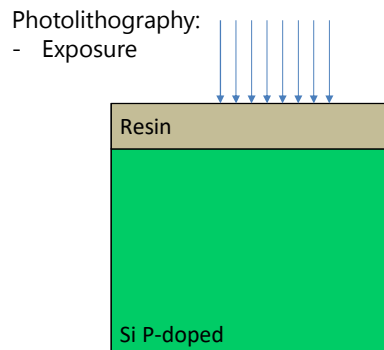
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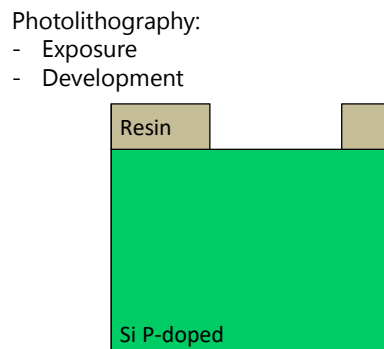
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## Process for a photodiode



- PN junction
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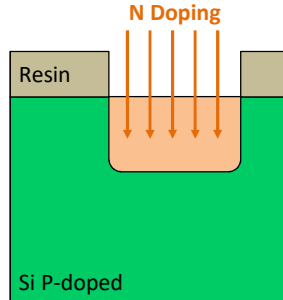


## Process for a photodiode



- PN junction
  - Based on P-doped silicon substrate (e.g. dopant Bore)
  - Local ion implant of N-doping (e.g. Phosphor)

Ion implantation

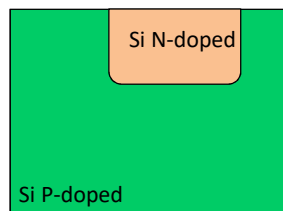


## Process for a photodiode



- PN junction
  - Based on P-doped silicon substrate (e.g. dopant Bore)
  - Local ion implant of N-doping (e.g. Phosphor)

Resin stripping

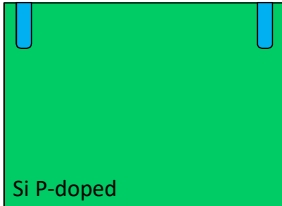


### Process for a transistor



- Source / drain: doped area
- Grid: control potential between S / D

STI (Shallow Trench Isolation) :

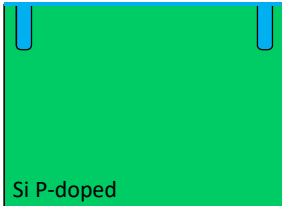


### Process for a transistor



- Source / drain: doped area
- Grid: control potential between S / D

Grid oxide deposition

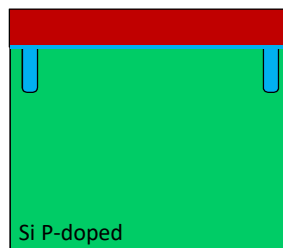


## Process for a transistor



- Source / drain: doped area
- Grid: control potential between S / D

Grid deposition (polycrystalline silicon)



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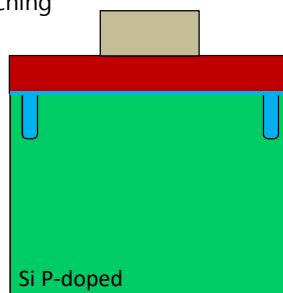
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## Process for a transistor



- Source / drain: doped area
- Grid: control potential between S / D

Grid localization  
 - photolithography  
 - etching



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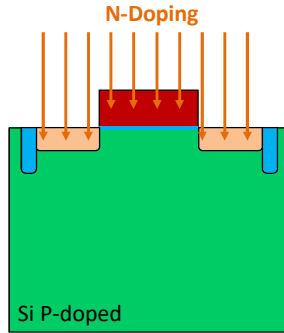


## Process for a transistor



- Source / drain: doped area
- Grid: control potential between S / D

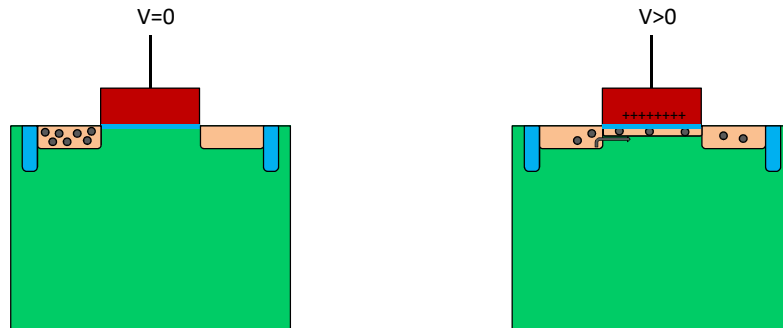
S/D implantation



## MOSFET transistor



- How does it works



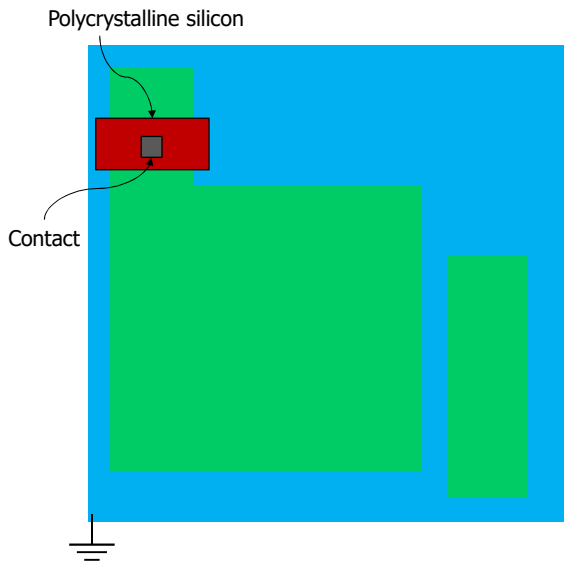
# How to draw it? 3T pixel layout



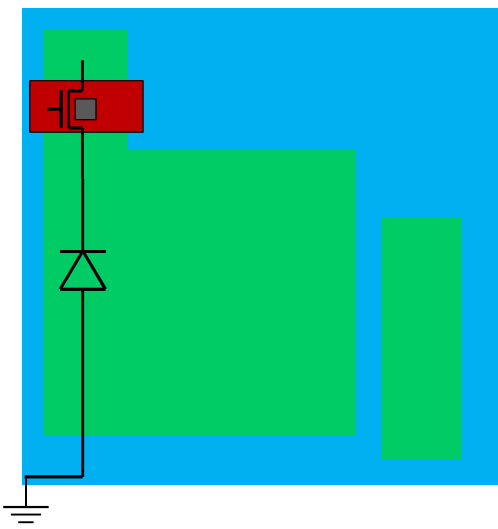
# 3T pixel layout



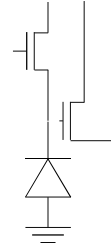
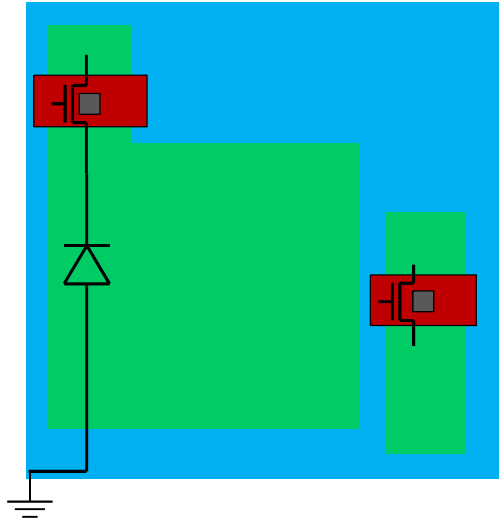
### 3T pixel layout



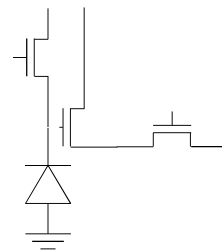
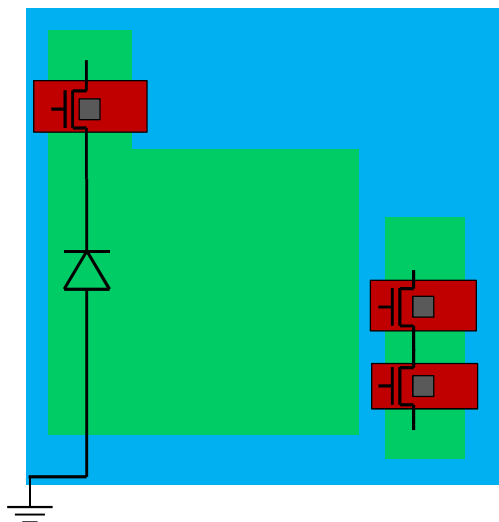
### 3T pixel layout



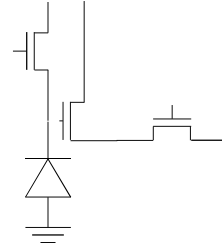
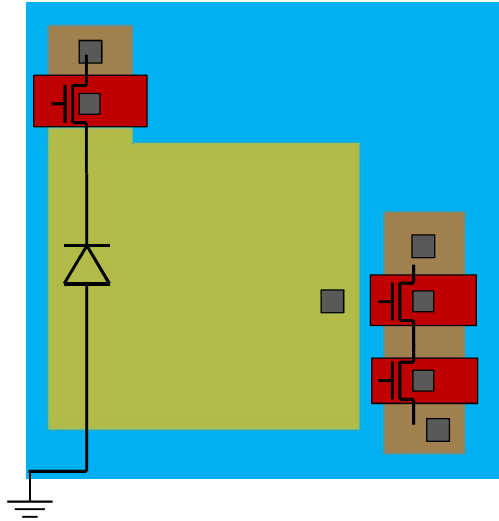
### 3T pixel layout



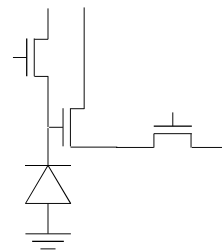
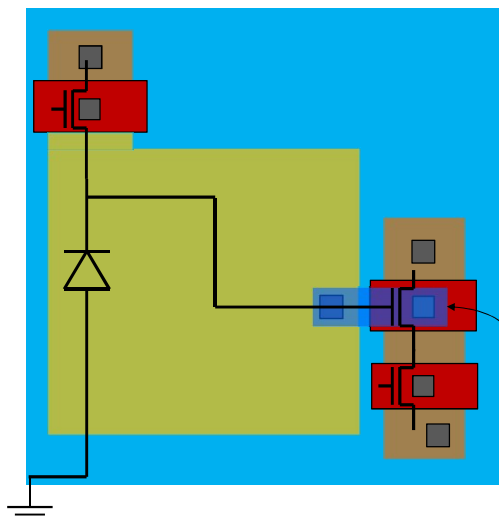
### 3T pixel layout



### 3T pixel layout

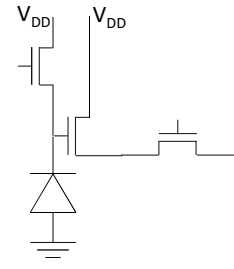
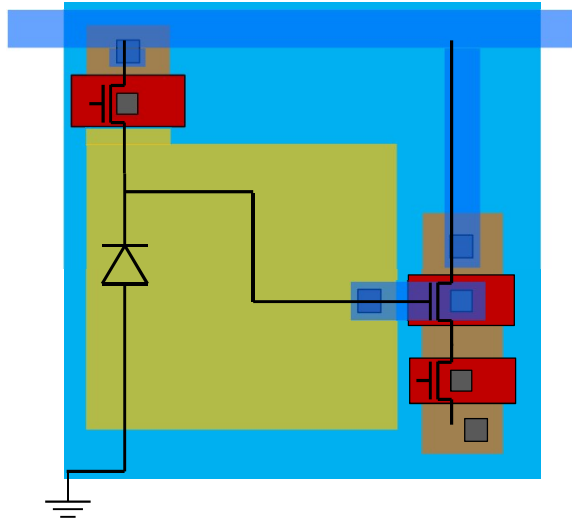


### 3T pixel layout

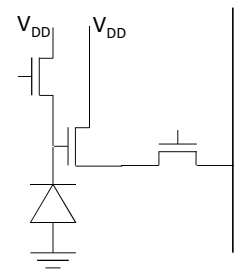
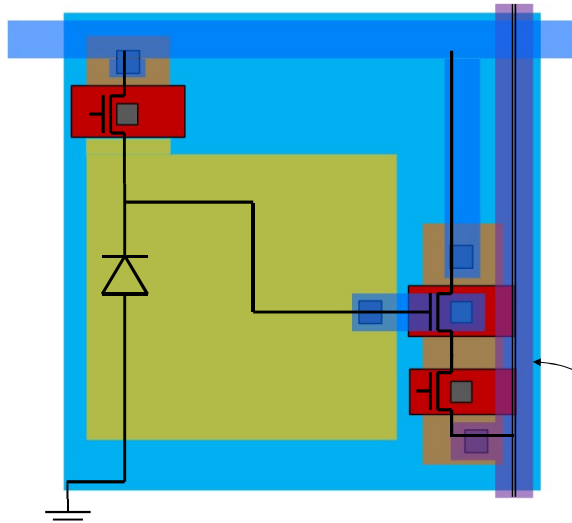


Metal 1

### 3T pixel layout

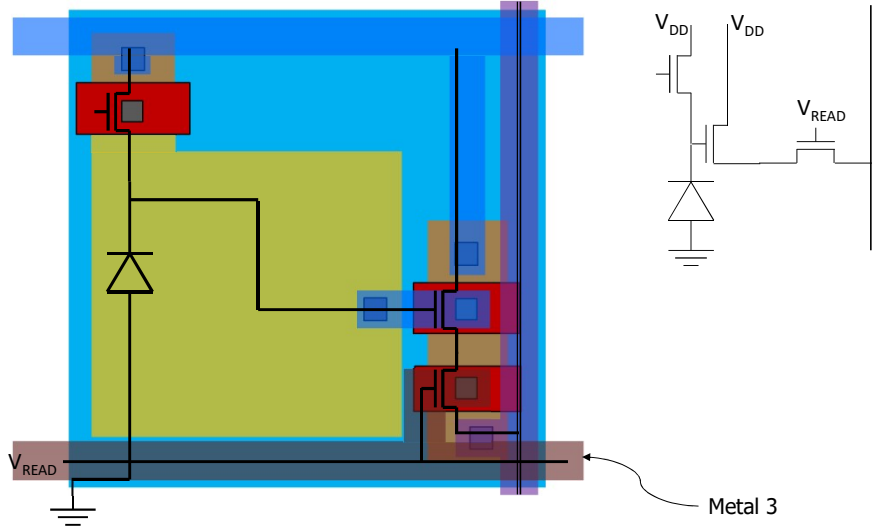


### 3T pixel layout

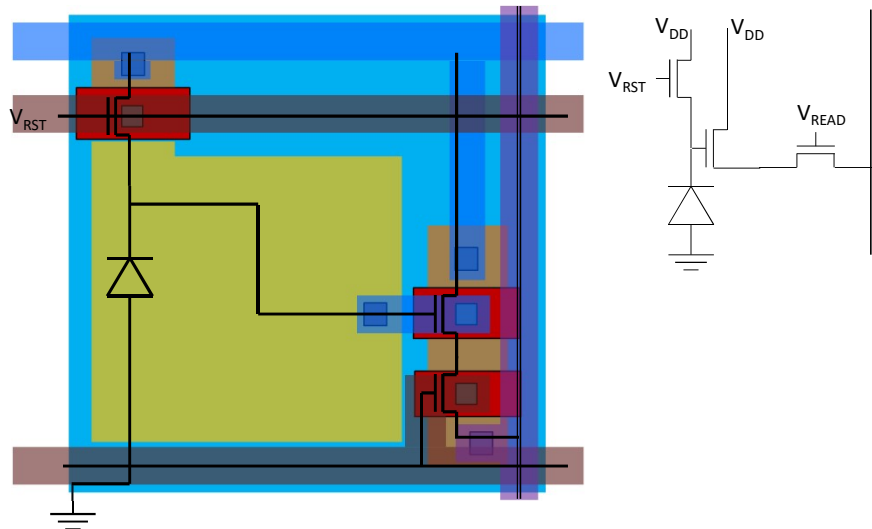


Metal 2

### 3T pixel layout



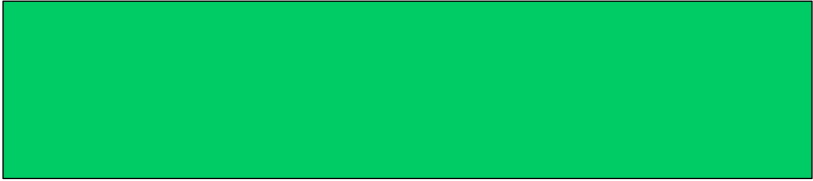
### 3T pixel layout



# Now, how to process it?

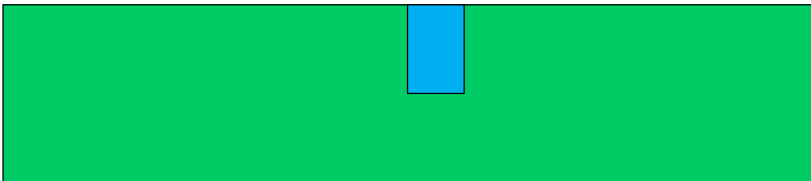


# CMOS process

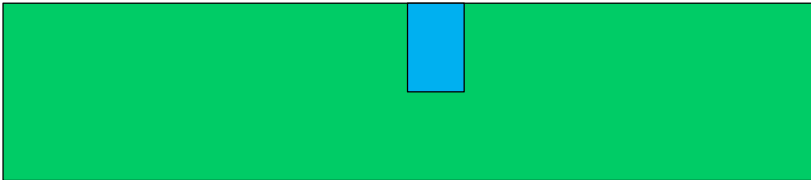




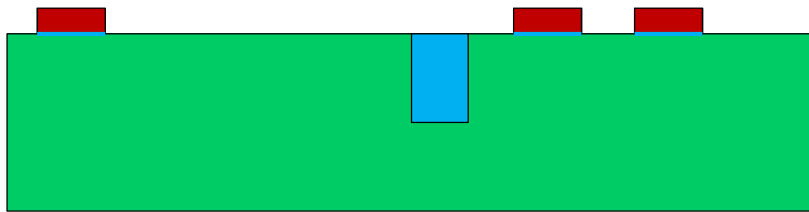
# CMOS process



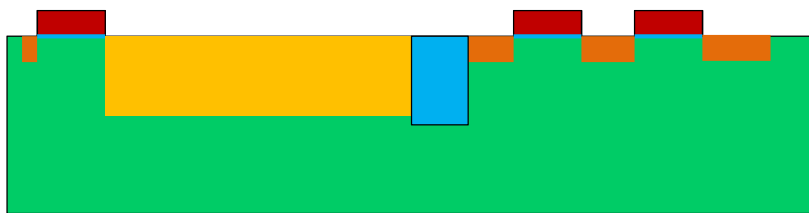
# CMOS process



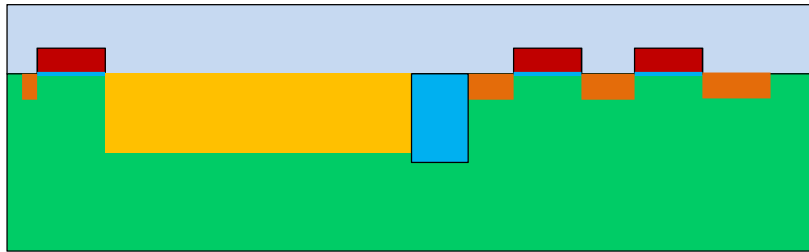
# CMOS process



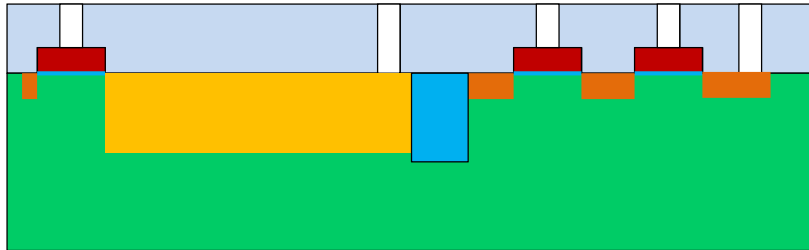
# CMOS process



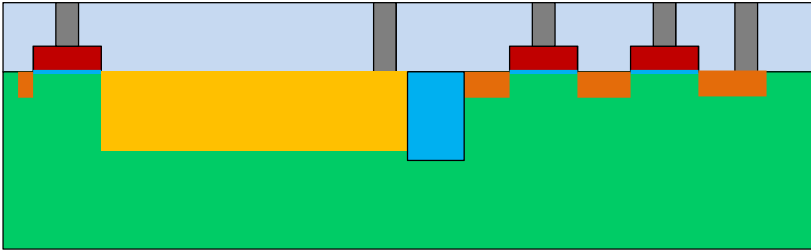
# CMOS process



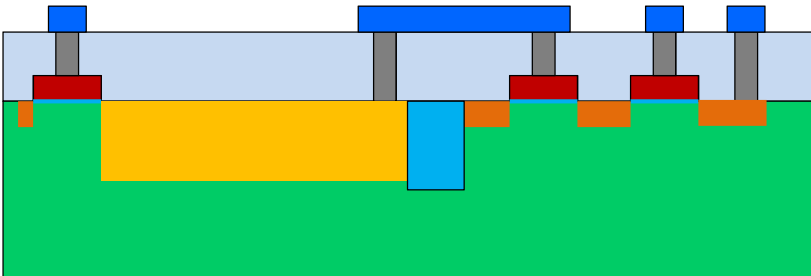
# CMOS process



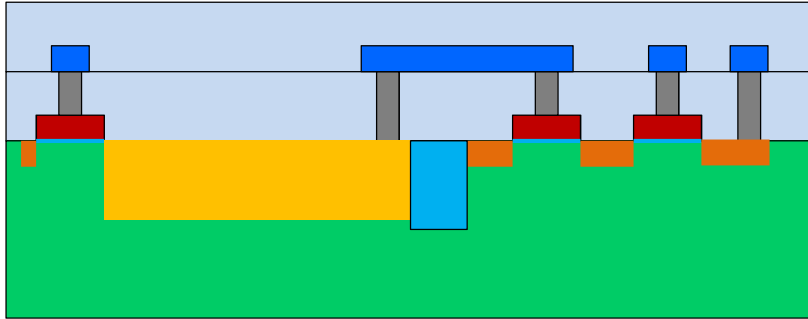
# CMOS process



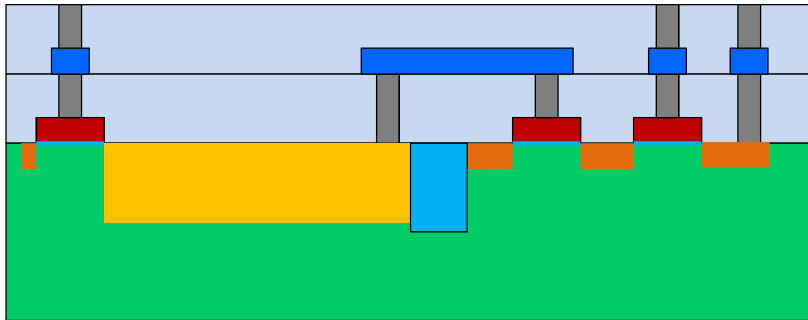
# CMOS process



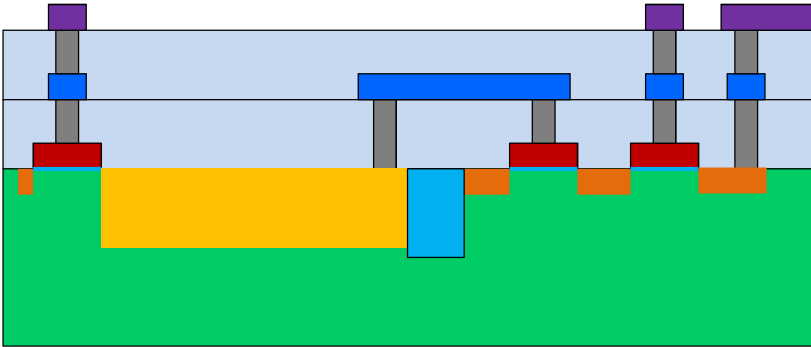
# CMOS process



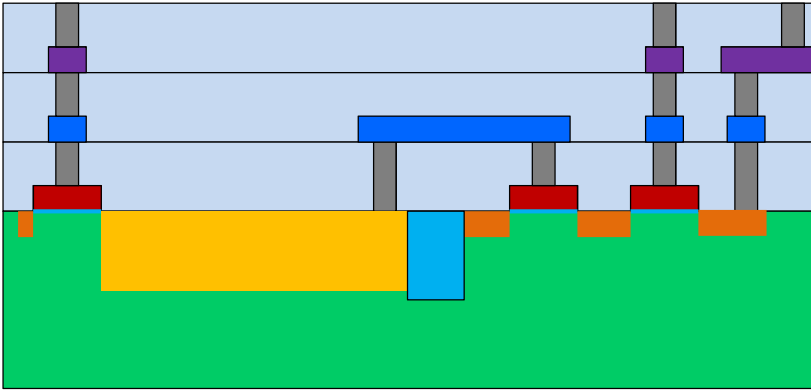
# CMOS process



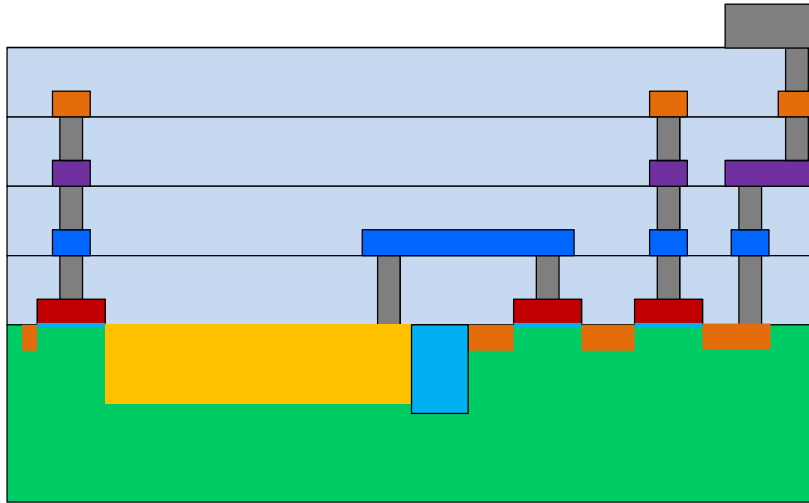
# CMOS process



# CMOS process



# CMOS process

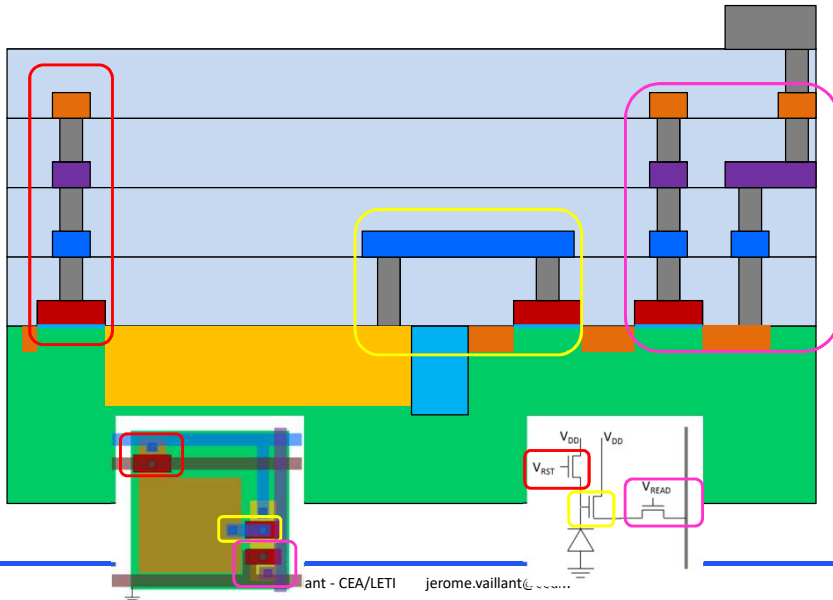


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